

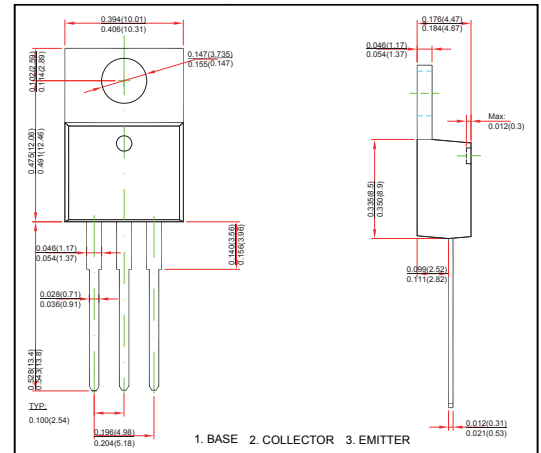
TO-220-3L Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Power Amplifier
- Complement to 2SB834
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-220-3L molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current -Continuous	I_C	3	A
Collector Power Dissipation	P_C	1.5	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=50mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			100	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=500mA$	60		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3A, I_B=300mA$			1	V
Base-emitter voltage	V_{BE}	$I_C=0.5A, V_{CE}=5V$			1	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=500mA$		3		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		70		pF
Turn on time	t_{on}	$I_{B1}=-I_{B2}=0.2A, I_C=2A$ $V_{CC}=30V, PW=20\mu s$		0.8		μs
Storage time	t_s			1.5		μs
Fall time	t_f			0.8		μs